

INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)

Docket Number (Optional)

YO998-426

Application Number

Not Yet Assigned

Applicant(s)

Cohn et al.

Filing Date

Concurrently Herewith

Group Art Unit

Not Yet Assigned

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
CK		5,102,819	04/07/1992	Matsushita et al.			
CK		5,120,666	06/09/1992	Gotou			
CK		5,166,084	11/24/1992	Pfiester			
CK		5,273,921	12/28/1993	Neudeck et al.			
CK		5,371,401	12/06/1994	Kurita			
CK		5,646,058	07/08/1997	Taur et al.			
CK		5,708,286	01/13/1998	Uesugi et al.			
CK		6,143,582	11/07/2000	Vu et al.			

J1050 U.S. PTO
10/05/1562
01/18/02

FOREIGN PATENT DOCUMENTS

REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO
CK	JP-05-226655	09/1993	Japan				

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

CK	Wong et al., "SELF-ALIGNED (TOP AND BOTTOM) DOUBLE-GATE MOSFET WITH A 25nm THICK SILICON CHANNEL", Electron Devices Meeting, 1997, Technical Digest, International, 1997, pp. 427-430
CK	Lee et al., "SUPER SELF-ALIGNED DOUBLE-GATE (SSDG) MOSFETs UTILIZING OXIDATION RATE DIFFERENCE AND SELECTIVE EPITAXY", IEDM, December 5, 1999, IEEE 1999

EXAMINER

Christy Kovacek

DATE CONSIDERED

2/6/03

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.